

PATENT ASSIGNMENT COVER SHEET

Electronic Version v1.1
 Stylesheet Version v1.2

EPAS ID: PAT4823166

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	RELEASE OF SECURITY INTEREST

CONVEYING PARTY DATA

Name	Execution Date
SILICON VALLEY BANK	02/05/2018

RECEIVING PARTY DATA

Name:	AVOGY, INC.
Street Address:	677 RIVER OAKS PARKWAY
City:	SAN JOSE
State/Country:	CALIFORNIA
Postal Code:	95134

PROPERTY NUMBERS Total: 79

Property Type	Number
Application Number:	13079710
Application Number:	13180758
Application Number:	13301165
Application Number:	13326192
Application Number:	13198655
PCT Number:	US2012049549
Application Number:	13198659
PCT Number:	US2012049520
PCT Number:	US2012048194
Application Number:	13198661
Application Number:	13198666
Application Number:	13225345
PCT Number:	US2012062728
Application Number:	13289219
Application Number:	13935345
Application Number:	13267552
Application Number:	13270606
PCT Number:	US2012056101
Application Number:	13240877
PCT Number:	US2012059245

PATENT

Property Type	Number
Application Number:	13270625
Application Number:	13315705
Application Number:	13300009
Application Number:	13300028
Application Number:	14062724
Application Number:	13312055
Application Number:	13299227
Application Number:	13932290
PCT Number:	US2012065954
Application Number:	13335572
PCT Number:	US2012068972
Application Number:	13335329
Application Number:	13307108
Application Number:	14061741
PCT Number:	US2012059250
Application Number:	13270641
PCT Number:	US2012062717
Application Number:	13299254
Application Number:	13335355
PCT Number:	US2012066669
Application Number:	13315720
PCT Number:	US2012069251
Application Number:	13334742
Application Number:	13465812
PCT Number:	US2012069299
Application Number:	13334514
Application Number:	13335383
Application Number:	13529822
Application Number:	13468325
Application Number:	13468332
Application Number:	13675694
Application Number:	13552365
PCT Number:	US2013053702
Application Number:	13572408
Application Number:	13586330
PCT Number:	US2013053751
Application Number:	13585121
Application Number:	13611467

Property Type	Number
Application Number:	13692717
Application Number:	13571743
Application Number:	13675916
Application Number:	13689574
PCT Number:	US2013069469
Application Number:	13675826
PCT Number:	US2013071522
Application Number:	13731872
PCT Number:	US2013076007
Application Number:	13735897
Application Number:	13730619
PCT Number:	US2013076009
Application Number:	13735912
Application Number:	13721542
Application Number:	14077039
Application Number:	13866286
Application Number:	13901546
Application Number:	14045708
Application Number:	14071032
Application Number:	14095759
Application Number:	14083217

CORRESPONDENCE DATA

Fax Number: (650)326-2422

Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.

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Email: kalvarez@kilpatricktownsend.com

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Address Line 1: KILPATRICK TOWNSEND & STOCKTON LLP

Address Line 2: 1100 PEACHTREE STREET, SUITE 2800

Address Line 4: ATLANTA, GEORGIA 30309

ATTORNEY DOCKET NUMBER: 102584-1044579-000000US

NAME OF SUBMITTER: KRISTINA ALVAREZ

SIGNATURE: /Kristina Alvarez/

DATE SIGNED: 02/13/2018

Total Attachments: 16

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RELEASE OF SECURITY INTEREST IN INTELLECTUAL PROPERTY

Effective February 5, 2018

WHEREAS, AVOGY, INC. (the "Company") entered into that certain Loan and Security Agreement dated as of March 21, 2014 (as amended, amended and restated, restated, supplemented modified or otherwise in effect from time to time (the "Agreement"), with SILICON VALLEY BANK (the "Secured Party"). Capitalized terms used herein but otherwise not defined herein shall have the meanings ascribed to them in the Agreement;

WHEREAS, pursuant to the Agreement, the Company executed and delivered to the Secured Party that certain Intellectual Property Security Agreement, dated as of March 21, 2014 (as amended, amended and restated, restated, supplemented modified or otherwise in effect from time to time, the "Grant"), which Grant was recorded with the United States Patent and Trademark Office on April 1, 2014 at Reel 032611, Frame 0010; and

WHEREAS, pursuant to the Grant and the Agreement, the Company granted to the Secured Party a security interest in certain intellectual property of the Company as set forth in Exhibit A (Copyrights), Exhibit B (Patents), Exhibit C (Trademarks), and Exhibit D (Mask Works) of the Agreement, collectively the "Intellectual Property". Copies of Exhibits A, B, C and D of the Agreement are attached hereto as Exhibits A, B, C and D, respectively.

NOW, THEREFORE, for valuable consideration, the receipt and sufficiency of which are hereby acknowledged, the Secured Party, without representation, warranty or recourse, hereby terminates and releases its security interest in the Intellectual Property, effective as of the date set forth above.

The Secured Party acknowledges that this document may be filed with the United States Patent and Trademark Office to evidence the termination and release granted herein.

[Signature Page Follows]

(Signature Page to Release of Security Interest in Patents)

SILICON VALLEY BANK

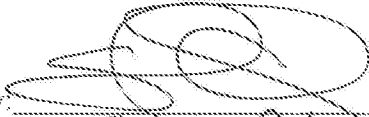
By: 
Name: Sheila Carlson
Title: Manager Director

EXHIBIT A

Copyrights

N/A

EXHIBIT B

Patents

FILE NO.	FAMILY NO.	CLIENT NO.	TITLE	COUNTRY	APPL. NO.	FILING DATE	PUB. NO.	PUB. DATE	PATENT NO.	ISSUE DATE	STATUS	INVENTORS
93444-818757	000100US	EP80001	CONTROLLED DOPING IN THE V-MATERIALS	United States of America	13079710	4/4/11	US-2012-0248577-A1	10/4/12			Published	Linda T. Romano, Dave P. Bour, Isik C. Kizilyalli, Hui Nie, Thomas R. Prunty
93444-818760	000300US	EP80003	ELECTRICAL ISOLATION OF HIGH DEFECT DENSITY REGIONS IN A SEMICONDUCTOR DEVICE	United States of America	13180758	7/12/11	US-2013-0912502-9A1	1/17/13			Published	Isik C. Kizilyalli, Dave P. Bour, Richard J. Brown, Andrew P. Edwards, Hui Nie, Linda Romano
93444-826397	000400US	EP80004	EDGE TERMINATION BY ION IMPLANTATION IN GAN	United States of America	13301165	11/21/11	US-2013-0126888-A1				Published	Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Linda Romano, Dave P. Bour, Richard J. Brown, Thomas R. Prunty
93444-826382	000500US	EP80005	IN GAN ORBIC SOURCE CONTACTS FOR VERTICAL POWER DEVICES	United States of America	13336192	12/16/11	US-2013-0153917-A1				Published	Linda Romano, Andrew P. Edwards, Dave P. Bour, Isik C. Kizilyalli
93444-808244	000600US	EP80006	METHOD AND SYSTEM FOR A GAN VERTICAL JET UTILIZING A REBROWN GATE	United States of America	13198653	8/4/11	US-2013-0832811-A1	2/7/13			Published	Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Linda Romano, Dave P. Bour, Richard J. Brown, Thomas R. Prunty
93444-816393	000610PC	EP80006PC	METHOD AND SYSTEM FOR A GAN VERTICAL JET UTILIZING A REBROWN GATE	PCT	PCT/US2012049549	8/3/12	WO 2013/020061	2/7/13			Published	Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Linda Romano, Dave P. Bour, Richard J. Brown, Thomas R. Prunty

93444- 808236	0097000US	EP8- 0007	METHOD AND SYSTEM FOR A GAN VERTICAL JET UTILIZING A REBORWN CHANNEL.	United States of America	13198659	8/4/11	US-2013- 0832812-A1	2/7/13	Published	Isik C. Kizilyall, Hui Nie, Andrew P. Edwards, Linda Romano, Dave P. Bour, Richard J. Brown, Thomas R. Prunty
93444- 846589	000710PC	EP8- 0007PC	METHOD AND SYSTEM FOR A GAN VERTICAL JET UTILIZING A REBORWN CHANNEL.	PCT	PCTUS1249520	8/3/12	WO 2013/020051	2/7/13	Published	Isik C. Kizilyall, Hui Nie, Andrew P. Edwards, Linda Romano, Dave P. Bour, Richard J. Brown, Thomas R. Prunty
93444- 846593	000800PC	EP8- 0008PC	METHOD AND SYSTEM FOR DOPING CONTROL IN GALLIUM NITRIDE BASED DEVICES	PCT	PCTUS2012048104	7/25/12	WO 2013/019521	2/7/13	Published	Isik C. Kizilyall, Hui Nie, Andrew P. Edwards, Linda Romano, Dave P. Bour, Richard J. Brown, Thomas R. Prunty
93444- 808237	000800US	EP8- 0008	METHOD AND SYSTEM FOR DOPING CONTROL IN GALLIUM NITRIDE BASED DEVICES	United States of America	13198681	8/4/11	US-2013- 0032813-A1	2/7/13	Published	Isik C. Kizilyall, Hui Nie, Andrew P. Edwards, Linda Romano, Dave P. Bour, Richard J. Brown, Thomas R. Prunty
93444- 808232	000900US	EP8-0009	METHOD AND SYSTEM FOR FORMATION OF P- N JUNCTIONS IN GALLIUM NITRIDE BASED ELECTRONICS	United States of America	11198666	8/4/11	US-2013- 0032814-A1	2/7/13	Published	David P. Bour, Thomas R. Prunty, Linda Romano, Andrew P. Edwards, Isik C. Kizilyall, Hui Nie, Richard J. Brown, Madhan M. Raj
93444- 808261	001000US	EP8-0010	METHOD AND SYSTEM FOR LOCAL CONTROL OF DEFECT DENSITY IN GALLIUM NITRIDE BASED ELECTRONICS	United States of America	13225345	9/27/11	US-2013- 0056743-A1		Published	David P. Bour, Linda Romano, Thomas R. Prunty, Isik C. Kizilyall, Hui Nie, Andrew P. Edwards, Richard J. Brown

93444-856390	001100PC	EP5-011PC	MONOLITHICALLY INTEGRATED VERTICAL JET AND SCHOTTKY DIODE	PCT	PCTUS2012062728	10/31/12	WO 2013/066967	Published	Isik C, Kizilyalli, Hai Nie, Andrew P, Edwards, Linda Romano, Dave P Bour, Richard J, Brown, Thomas R, Prunty
93444-81381	001100US	EP5001	MONOLITHICALLY INTEGRATED VERTICAL JET AND SCHOTTKY DIODE	United States of America	13289219	11/4/11	US-2013-0112983-A1	Issued	Isik C, Kizilyalli, Hai Nie, Andrew P, Edwards, Linda Romano, David P, Bour, Richard J, Brown, Thomas R, Prunty
93444-880165	001100US	EP5-0011-1	MONOLITHICALLY INTEGRATED VERTICAL JET AND SCHOTTKY DIODE	United States of America	13915345	7/3/13		Pending	Isik C, Kizilyalli, Hai Nie, Andrew P, Edwards, Linda Romano, Dave P, Bour, Richard J, Brown, Thomas R, Prunty
93444-813833	001200US	EP50012	MONOLITHICALLY INTEGRATED HEAT AND SCHOTTKY DIODE	United States of America	13267582	10/6/11	US-2013-0087803-A1	Published	Kizilyalli Isik C, Nie Hai, Edwards Andrew P., Romano Linda, David P Bour, Brown Richard J., Prunty Thomas R.
93444-816904	001300US	EP50013	METHOD AND SYSTEM FOR FLOATING GUARD RINGS IN GAN MATERIALS	United States of America	13270696	10/11/11	US-2013-0087835-A1	Published	Andrew P, Edwards, Hai Nie, Isik C, Kizilyalli, Richard J, Brown, Dave P, Bour, Linda Romano, Thomas R, Prunty
93444-852922	001400PC		METHOD AND SYSTEM FOR DIFFUSION AND IMPARTATION IN GALLIUM NITRIDE BASED DEVICES	PCT	PCTUS2012056101	9/19/12		Pending	Dave P, Bour, Richard J, Brown, Isik C, Kizilyalli, Thomas R, Prunty, Linda Romano, Andrew P, Edwards, Hai Nie, Medhro M, Raj

93444- 816905	001400US	EP99014	METHOD AND SYSTEM FOR DIRECTION AND IMPLANTATION IN GALLIUM NITRIDE BASED DEVICES	United States of America	13240877	9/22/11	US-2013- 0075746-A1	3/28/13	Published	Dave P. Bour, Richard J. Brown, Kirk C. Kizilyalli, Thomas R. Prunty, Linda Romano, Andrew P. Edwards, Hai Nie, Madhan M. Raj
93444- 819244	001500US	EP8- 0015	METHOD OF FABRICATING A GALLIUM NITRIDE MERGED P-LIN SCHOTTKY (MPS) DIODE	United States of America	13270625	10/11/11	US-2013- 0087878-A1	4/11/13	Published	Andrew P. Edwards, Hai Nie, Kirk C. Kizilyalli, Linda Romano, Dave P. Bour, Richard J. Brown, Thomas R. Prunty
93444- 851214	001510PC	EP5- 0015PC	METHOD OF FABRICATING A GAN MERGED P-LIN SCHOTTKY (MPS) DIODE	PCT	PCTUS201259245	10/8/12	WO 2013/055629		Published	Andrew P. Edwards, Hai Nie, Kirk C. Kizilyalli, Linda Romano, Dave P. Bour, Richard J. Brown, Thomas R. Prunty
93444- 819311	001600US	EP99016	VERTICAL GAN-BASED METAL INSULATOR SEMICONDUCTOR FET	United States of America	13315705	12/9/11	US-2013- 0146885-A1		Issued	Richard J. Brown, Hai Nie, Andrew Edwards, Kirk Kizilyalli, David Bour, Thomas Prunty, Linda Romano, Madhan Raj
93444- 819313	001700US	EP99017	GAN-BASED SCHOTTKY BARRIER DIODE WITH ALGAN SURFACE LAYER	United States of America	13300099	11/18/11	US-2013- 0126886-A1		Published	Richard J. Brown, Thomas R. Prunty, Dave P. Bour, Kirk C. Kizilyalli, Hai Nie, Andrew P. Edwards, Linda Romano, Madhan M. Raj
93444- 819312	001800US	EP99018	GAN-BASED SCHOTTKY BARRIER DIODE WITH FIELD PLATE	United States of America	13300028	11/18/11	US-2013- 0127006-A1		Issued	Madhan Raj, Richard J. Brown, Thomas R. Prunty, David P. Bour, Kirk C. Kizilyalli, Hai Nie, Andrew P. Edwards, Linda Romano

93444-891731	001891US	EP80019	GAN-BASED SCHOTTKY BARRIER DIODE WITH FIELD PLATE	United States of America	14062724	10/24/13	US-2014-0051236-A1	Published	Madsen Raj, Richard J. Brown, Thomas R. Premy, David P. Bour, Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Itzhak Romano
93444-819314	001900US	EP80019	IN-SITU SIM GROWTH TO ENABLE SCHOTTKY CONTACT FOR GAN DEVICES	United States of America	13912055	12/6/11	US-2013-0143392-A1	Published	Linda Romano, Dave P. Bour, Andrew P. Edwards, Hui Nie, Isik C. Kizilyalli, Richard J. Brown, Thomas R. Premy
93444-819315	002090US	EP80020	ALUMINUM GALLIUM NITRIDE EPOCH STOP LAYER FOR GALLIUM NITRIDE BASES DEVICES	United States of America	13299227	11/17/11	US-2013-0126884-A1	Published	Linda Romano, Andrew P. Edwards, Richard J. Brown, Dave P. Bour, Hui Nie, Isik C. Kizilyalli, Thomas R. Premy, Madsen M. Raj
93444-820283	002010US	EP8-0020-1	ALUMINUM GALLIUM NITRIDE EPOCH STOP LAYER FOR GALLIUM NITRIDE BASED DEVICES	United States of America	13932290	7/1/13		Pending	Linda Romano, Andrew P. Edwards, Richard J. Brown, David P. Bour, Hui Nie, Isik C. Kizilyalli, Thomas R. Premy, Madsen Raj
93444-832908	002100PC	W021PC	METHOD AND SYSTEM FOR A GAN SELF-ALIGNED VERTICAL MESFET	PCT	PCTUS2012068974	11/20/12	WO 2013/095847	Published	Richard J. Brown, Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Dave P. Bour
93444-823390	002100US	EP8-0021	METHOD AND SYSTEM FOR A GAN SELF-ALIGNED VERTICAL MESFET	United States of America	13335572	12/22/11	US-2013-0161635-A1	Published	Richard J. Brown, Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Dave P. Bour
93444-839134	002200PC	EP8-0022PC	METHOD OF FABRICATING A GALLIUM NITRIDE P-I-N DIODE USING IMPLANTATION	PCT	PCTUS2012068972	12/11/12	WO 2013/096013	Published	Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Richard J. Brown, Donald R. Desany
93444-819316	002200US	EP8-0022	METHOD OF FABRICATING A GAN P-I-N DIODE USING IMPLANTATION	United States of America	13335329	12/22/11	US-2013-0161780-A1	Published	Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Richard J. Brown, Donald R. Desany

93444- 824393	002310US	EP80023	METHOD AND SYSTEM FOR CARBON DOPING CONTROL IN GALLIUM NITRIDE BASED DEVICES	United States of America	13307106	11/20/11	US-2013- 0137225-A1	8569153	10/29/13	Issued	David P. Bour, Thomas R. Prunty, Linda Romano, Richard J. Brown, Isik C. Kizilyalli, Hui Nie
93444- 821183	002310US	EP8- 0023-1	METHOD AND SYSTEM FOR CARBON DOPING CONTROL IN GALLIUM NITRIDE BASED DEVICES	United States of America	14061741	10/23/13				Pending	David P. Bour, Thomas R. Prunty, Linda Romano, Richard J. Brown, Isik C. Kizilyalli, Hui Nie
93444- 854261	002400PC	EP8- 0024PC	SCHOTTKY DIODE WITH BURIED LAYER IN GAN MATERIALS	PCT	PCTUS201239250	10/8/12	WO 2013/055631			Published	Andrew P. Edwards, Hui Nie, Isik C. Kizilyalli, Richard J. Brown, David P. Bour, Linda Romano, Thomas R. Prunty
93444- 822319	002400US	EP-0024	SCHOTTKY DIODE WITH BURIED LAYER IN GAN MATERIALS	United States of America	13270641	10/11/11	US-2013- 0987879-A1		4/11/13	Published	Andrew P. Edwards, Hui Nie, Isik C. Kizilyalli, Richard J. Brown, Dave P. Bour, Linda Romano, Thomas R. Prunty
93444- 856389	002500PC	EP8- 0025PC	METHOD AND SYSTEM FABRICATING FLOATING GUARD RINGS IN GAN MATERIALS	PCT	PCTUS2012062717	10/31/12	WO 2013/074291			Published	Donald R. Disney, Andrew P. Edwards, Hui Nie, Richard J. Brown, Isik C. Kizilyalli, Dave P. Bour, Linda Romano, Thomas R. Prunty
93444- 823950	002500US	EP8- 0025	METHOD AND SYSTEM FOR FABRICATING FLOATING GUARD RINGS IN GAN MATERIALS	United States of America	13292254	11/17/11	US-2013- 0126865-A1			Allowed	Donald R. Disney, Andrew P. Edwards, Hui Nie, Richard J. Brown, Isik C. Kizilyalli, Dave P. Bour, Linda Romano, Thomas R. Prunty
93444- 824394	002600US	EP80026	FABRICATION OF FLOATING GUARD RINGS USING SELECTIVE REGROWTH	United States of America	13335355	12/22/11	US-2013- 0164893-A1	8592298	11/26/13	Issued	Linda Romano, David P. Bour, Andrew Edwards, Hui Nie, Isik C. Kizilyalli, Richard J. Brown, Thomas R. Prunty

93444-824395	002700US	EP-	0027	VERTICAL GAN JET WITH GATE SOURCE ELECTRODES ON REGROWN GATE	United States of America	13315720	12/9/11	US-2013-0146886-A1	Allowed	Donald R. Disney, Hui Nie, Jark C. Kitzlyall, Richard J. Brown
93444-837888	002710PC	EP-	0027PC	VERTICAL GAN JET WITH GATE AND SOURCE ELECTRODES ON REGROWN GATE	PCT	PCTUS2012066669	11/27/12	WO 2013/085748	Published	Donald R. Disney, Hui Nie, Jark C. Kitzlyall, Richard J. Brown
93444-837874	002400PC	EP-	0028PC	METHOD AND SYSTEM FOR JUNCTION TERMINATION IN GAN MATERIALS USING CONDUCTIVITY MODULATION	PCT	PCTUS2012069251	12/12/12	WO 2013/098054	Published	Hui Nie, Andrew P. Edwards, Donald R. Disney, Richard J. Brown, Jark C. Kitzlyall
93444-824392	002800US	EP-	0028	METHOD AND SYSTEM FOR JUNCTION TERMINATION IN GAN MATERIALS USING CONDUCTIVITY MODULATION	United States of America	13334742	12/22/11	US-2013-0161633-A1	Allowed	Hui Nie, Andrew P. Edwards, Donald R. Disney, Richard J. Brown, Jark C. Kitzlyall
93444-824381	002900US	EP-	0029	METHOD AND SYSTEM FOR PLANAR REGROWTH IN GAN ELECTRONIC DEVICES	United States of America	13465812	5/7/12	US-2013-0292686-A1	Published	Jark C. Kitzlyall, Linda Romano, Dave P. Bour
93444-859133	003090PC	EP-	0030PC	METHOD AND SYSTEM FOR A GALLIUM NITRIDE VERTICAL JET WITH SELF-ALIGNED SOURCE AND GATE	PCT	PCTUS2012069259	12/12/12	WO 2013/098062	Published	Donald R. Disney, Jark C. Kitzlyall, Hui Nie, Linda Romano, Richard J. Brown, Madhan M. Raj
93444-826389	003000US	EP-	0030	METHOD AND SYSTEM FOR A GAN VERTICAL JET WITH SELF-ALIGNED SOURCE AND GATE	United States of America	13334514	12/22/11	US-2013-0161705-A1	Published	Donald R. Disney, Jark C. Kitzlyall, Hui Nie, Linda Romano, Richard J. Brown, Madhan M. Raj
93444-826379	003100US	EP-	0031	METHOD AND SYSTEM FOR FABRICATING EDGE TERMINATION STRUCTURES IN GAN MATERIALS	United States of America	13335383	12/22/11	US-2013-0161634-A1	Allowed	Donald R. Disney, Jark C. Kitzlyall, Linda Romano, Andrew P. Edwards, Hui Nie
93444-833448	003200US	EP-	0032	GAN VERTICAL SUPERJUNCTION DEVICE STRUCTURE AND FABRICATION METHODS	United States of America	13529822	6/21/12	US-2013-0341677-A1	Published	Hui Nie, Andrew P. Edwards, Donald R. Disney, Jark C. Kitzlyall

93444- 833469	003300US	EP8- 0033	METHOD AND SYSTEM FOR A GALLIUM NITRIDE VERTICAL JET WITH SELF- ALIGNED GATE METALLIZATION	United States of America	13468325	5/10/12	US-2013- 0299873-A1	Allowed	Donald R. Disney, Richard J. Brown, Hai Nie
93444- 839418	003310US	EP8- 0033.1	METHOD AND SYSTEM FOR A GAN VERTICAL JET WITH SELF- ALIGNED SOURCE METALLIZATION	United States of America	13468332	5/10/12	US-2013- 0299882-A1	Allowed	Donald R. Disney, Richard J. Brown, Hai Nie
93444- 833463	003400US	EP9- 0034	VERTICAL GAN JET WITH LOW GATE DRAIN CAPACITANCE AND HIGH GATE SOURCE CAPACTANCE	United States of America	13575694	11/13/12		Pending	Donald R. Disney
93444- 820540	003900US	EP8- 0035	GAN POWER DEVICE WITH SOLIDERABLE BACK METAL	United States of America	13552365	7/18/12	US-2014- 0921479-A1	Published	Patrik James Lardo Hyland, Brian Alvarez, Donald R. Disney
93444- 863361	003600PC	EP8- 0036-PC	METHOD AND SYSTEM FOR GALLIUM NITRIDE ELECTRONIC DEVICES USING ENGINEERED SUBSTRATES	PCT	PCTUS2013051702	6/6/13	W/O 2014025172	Published	Hui Nie, Donald R. Disney, Isik C. Kizilyalli
93444- 840541	003600US	EP8- 0036	METHOD AND SYSTEM FOR GALLIUM NITRIDE ELECTRONIC DEVICES USING ENGINEERED SUBSTRATES	United States of America	13572408	8/10/12	US-2014- 0042447-A1	Published	Hui Nie, Donald R. Disney, Isik C. Kizilyalli
93444- 840542	003700US	EP8- 0037	METHOD AND SYSTEM FOR EDGE TERMINATION IN GAN MATERIALS BY SELECTIVE ARPA IMPLANTATION DOPING	United States of America	13586330	8/15/12	US-2014- 0048903-A1	Published	Andrew Edwards, Hui Nie, Isik C. Kizilyalli, Dave Bour
93444- 883362	003800PC	EP8- 0038-PC	METHOD OF FABRICATING A GALLIUM NITRIDE MERGED P-LIN SCHOTKY (MPS) DIODE BY REGROWTH AND ETCH BACK	PCT	PCTUS2013053751	8/6/13		Pending	Hakham M. Raj, Briton Alvarez, Dave P. Bour, Andrew P. Edwards, Hui Nie, Isik C. Kizilyalli

93444- 840343	003800US	EPS- 0038	METHOD OF FABRICATING A GALLIUM NITRIDE MERGED PIN SCHOTTKY (MPS) DIODE BY REGROWTH AND ETCH BACK AND ETCH BACK CONDENSABLE TOP METAL CONTACTS FOR GALLIUM NITRIDE POWER DEVICES	United States of America	13585121	8/14/12	US-2014- 0048902-A1	Published	Madhan M. Raj, Brian Alvaraz, Dave P. Bour, Andrew P. Edwards, Hui Nie, Jank C. Kizilyalli
93444- 843972	003900US	EPS- 0039	AC-DC CONVERTER FOR WIDE RANGE OUTPUT VOLTAGE AND HIGH SWITCHING FREQUENCY	United States of America	13611467	9/27/12		Pending	Brian Joel Alvaraz, Dessald R. Dismey, Hui Nie, Patrick James Lerzo Hyland
93444- 843971	004000US	EPS- 0040	METHOD AND SYSTEM FOR IN-SITU AND REGROWTH IN GALLIUM NITRIDE BASED DEVICES	United States of America	13571743	8/1/07	US-2014- 0048306-A1	Published	David P. Bour, Thomas R. Prunty, Hui Nie, Madhan M. Raj
93444- 851061	004200US	EPS- 0042	GAN VERTICAL BIPOLAR TRANSISTOR	United States of America	13675916	11/13/12		Pending	Hui Nie, Andrew P. Edwards, Jank C. Kizilyalli, Dave Bour
93444- 831060	004300US	EPS- 0043	METHOD AND SYSTEM FOR GALLIUM NITRIDE VERTICAL JET WITH SEPARATED GATE AND SOURCE	United States of America	13689574	11/29/12		Pending	Hui Nie, Andrew P. Edwards, Dave P. Bour, Jank C. Kizilyalli, Richard J. Brown, Thomas R. Prunty
93444- 879231	004400PC	EPS- 0044	LATERAL GAN JET WITH VERTICAL DRIFT REGION	PCT	PCTUS2013069469	11/11/13		Pending	Hui Nie, Andrew Edwards, Jank Kizilyalli, Dave Bour, Thomas R. Prunty
93444- 851039	004400US	EPS- 0044	LATERAL GAN JET WITH VERTICAL DRIFT REGION	United States of America	13675826	11/13/12		Pending	Hui Nie, Andrew P. Edwards, Jank Kizilyalli, Dave Bour, Thomas R. Prunty
93444- 894149	004500PC	EPS- 0045-PC	HIGH POWER DENSITY OFF-LINE POWER SUPPLY	PCT	PCTUS2013071522	11/22/13		Pending	Hemal N. Shah
93444- 831038	004500US	EPS- 0045	HIGH POWER DENSITY OFF-LINE POWER SUPPLY	United States of America	13731872	12/31/12		Pending	Hemal N. Shah

93444-89561S	004600PC	EP8-0046-PC	GALLIUM NITRIDE VERTICAL JET WITH HEXAGONAL CELL STRUCTURE	PCT	PCTUS2013076007	12/18/13	Pending	Andrew P. Edwards, Hui Nie, Donald R. Disney, Itek C. Kizlyalli
93444-856299	004600US	EP8-0046	GALLIUM NITRIDE VERTICAL JET WITH HEXAGONAL CELL STRUCTURE	United States of America	13735897	1/7/13	Pending	Andrew P. Edwards, Hui Nie, Donald R. Disney, Itek C. Kizlyalli
93444-85630U	004700US	EP8-0047	METHOD AND SYSTEM FOR CO-PACKAGING GALLIUM NITRIDE ELECTRONICS	United States of America	13730619	12/28/12	Pending	Donald R. Disney, Hemanth N. Shah
93444-895614	004800PC	EP8-0048-PC	METHOD AND SYSTEM FOR A GALLIUM NITRIDE VERTICAL TRANSISTOR	PCT	PCTUS2013076009	12/18/13	Pending	Hui Nie, Andrew P. Edwards, Itek C. Kizlyalli, Dave P. Bour, Thomas R. Prunty, Quentin Diaback
93444-856302	004800US	EP8-0048	METHOD AND SYSTEM FOR A GALLIUM NITRIDE VERTICAL TRANSISTOR	United States of America	13734912	1/7/13	Pending	Hui Nie, Andrew P. Edwards, Itek C. Kizlyalli, Dave P. Bour, Thomas R. Prunty, Quentin Diaback
93444-856302	004900US	EP8-0049	VERTICAL GAN POWER DEVICE WITH BREAKDOWN VOLTAGE CONTROL	United States of America	13721342	12/20/12	Pending	Donald R. Disney
93444-868145	005000US	EP8-0050	GALLIUM NITRIDE FIELD EFFECT TRANSISTOR WITH BURIED FIELD PLATE PROTECTED LATERAL CHANNEL	United States of America	14077039	11/7/13	Pending	Ozgur Aktao, Itek C. Kizlyalli
93444-858147	005200US	EP8-0052	METHOD OF FABRICATING A MERGED P-N JUNCTION AND SCHOTTKY DIODE WITH BURIED GALLIUM NITRIDE LAYER	United States of America	13866286	4/19/13	Pending	Itek C. Kizlyalli, Dave P. Bour, Thomas R. Prunty, Hui Nie, Quentin Diaback, Ozgur Aktao
93444-873690	005300US	EP8-0053	METHOD AND SYSTEM FOR CO-PACKAGING VERTICAL GALLIUM NITRIDE POWER DEVICES	United States of America	13901546	5/23/13	Pending	Donald R. Disney, Hemanth N. Shah

93444- 873691	005400US 0054	EP-S-	METHOD AND SYSTEM FOR OPERATING GALLIUM NITRIDE ELECTRONICS	United States of America	14035708	10/3/13	Pending	Hemal N. Shah, Donald R. Disney, Henrich Arnikhetul Nannagordi
93444- 873610	005500US 0055	EP-S-	HIGH POWER GALLIUM NITRIDE ELECTRONICS USING MISCELL SUBSTRATES	United States of America	14071032	11/6/13	Pending	Isk C. Kozlyallu, Dawit P. Hoor, Thomas R. Prunty, Guangfeng Ye
93444- 873611	005600US 0056	EP-S-	AC-DC CONVERTER WITH ADJUSTABLE OUTPUT	United States of America	14095759	12/3/13	Pending	Hemal N. Shah, Vinod Khosla
93444- 880156	005700US 0057	EP-S-	METHOD AND SYSTEM FOR INTERLEAVED BOOST CONVERTER WITH CO-PACKAGED GALLIUM NITRIDE POWER DEVICES	United States of America	14083217	11/18/13	Pending	Hemal N. Shah, Donald R. Disney

EXHIBIT C

Trademarks

Pending Applications

<u>Mark</u>	<u>Country</u>	<u>Serial No.</u>	<u>Filing Date</u>
TRUE GAN	Australia (Madrid Protocol)	1533372	11/19/12
TRUE GAN	Singapore (Madrid Protocol)	T1219939A	11/19/12
TRUE GAN	Switzerland (Madrid Protocol)	1141080	11/19/12
TRUE GAN	United States	85/661149	06/25/12
TRUE GAN	Vietnam (Madrid Protocol)	1141080	11/19/12

Issued Registrations

<u>Mark</u>	<u>Country</u>	<u>Reg. No.</u>	<u>Reg. Date</u>
TRUE GAN	China (Madrid Protocol)	1141080	11/19/12
TRUE GAN	European Community (Madrid Protocol)	1141080	11/19/12
TRUE GAN	Madrid Protocol	1141080	11/19/12
TRUE GAN	Japan (Madrid Protocol)	1141080	11/19/12
TRUE GAN	Korea (Madrid Protocol)	1141080	11/19/12

EXHIBIT D

Mask Works

N/A